

# isc Silicon PNP Power Transistor

## 2SB1085

### DESCRIPTION

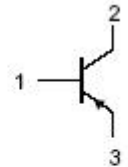
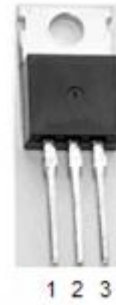
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -120V$  (Min)
- Wide Area of Safe Operation
- Complement to Type 2SD1562
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

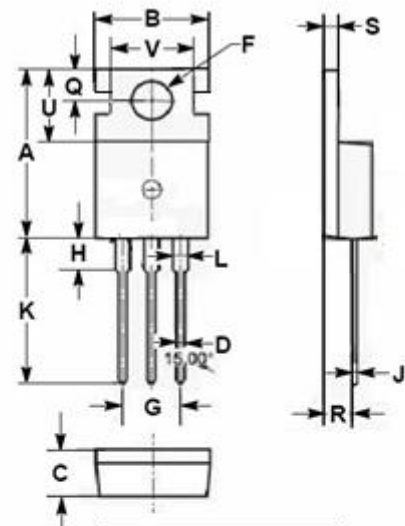
- Designed for low frequency power amplifier applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5.0	V
$I_C$	Collector Current-Continuous	-1.5	A
$I_{CM}$	Collector Current-Peak	-3	A
$P_C$	Total Power Dissipation @ $T_C=25^{\circ}C$	20	W
	Total Power Dissipation @ $T_a=25^{\circ}C$	1.5	
$T_J$	Junction Temperature	150	
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



PIN: 1 Base  
2 Collector  
3 Emitter  
TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

**isc Silicon PNP Power Transistor****2SB1085****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-120			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -50 μA; I <sub>E</sub> = 0	-120			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -50 μA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -0.1A			-2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -0.1A			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-1.0	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-1.0	μA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -0.1A; V <sub>CE</sub> = -5V	60		200	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.1A; V <sub>CE</sub> = -5V		50		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1MHz		30		pF

**◆ h<sub>FE</sub> Classifications**

D	E
60-120	100-200

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